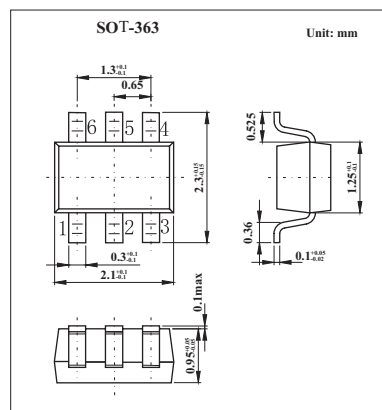


# BAT754L

## ■ Features

- Very low forward voltage
- Guard ring protected
- Low diode capacitance
- Three independent diodes in a small plastic SMD package.



## ■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Conditions	Min	Max	Unit
Per diode					
continuous reverse voltage	V <sub>R</sub>			30	V
continuous forward current	I <sub>F</sub>			200	mA
repetitive peak forward current	I <sub>FRM</sub>	t <sub>p</sub> ≤ 1 s; δ ≤ 0.5		300	mA
non-repetitive peak forward current	I <sub>FSM</sub>	t <sub>p</sub> < 10 ms		600	mA
storage temperature	T <sub>stg</sub>		-65	+150	°C
junction temperature	T <sub>j</sub>			125	°C
operating ambient temperature	T <sub>amb</sub>		-65	+125	°C
thermal resistance from junction to ambient	R <sub>th j-a</sub>			416	K/W

## ■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Conditions	Max	Unit
forward voltage	V <sub>F</sub>	I <sub>F</sub> = 0.1 mA	200	mV
		I <sub>F</sub> = 1 mA	260	
		I <sub>F</sub> = 10 mA	340	
		I <sub>F</sub> = 30 mA	420	
		I <sub>F</sub> = 100 mA	750	
reverse current	I <sub>R</sub>	V <sub>R</sub> = 25 V; note 1	2	μA
diode capacitance	C <sub>d</sub>	f = 1 MHz; V <sub>R</sub> = 1 V	10	pF

Note

1. Pulse test: t<sub>p</sub> = 300 μs; δ = 0.02.

## ■ Marking

Marking	L1
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